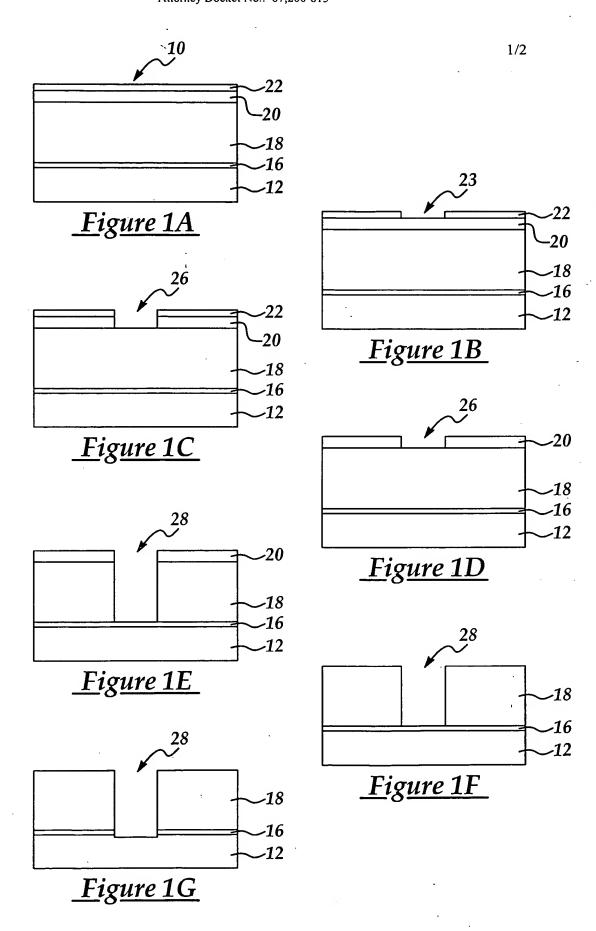
Tsai, et al Inventor(s): Serial No.: To Be Assigned

Filed: Herewith

For: A Bi-Layer Photoresist Dry Development ... Ion Etch Method

Attorney Docket No.: 67,200-613





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> **202 2**06 205 214 212 210 <u>Figure 2</u>

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-301 PHOTOMASK & DEVELOP TOP IMAGE LAYER DRY DEVELOP BOTTOM IMAGE LAYER -303 IN-SITU ASHING TOP IMAGE LAYER -305 (OPTIONAL) CONTACT ETCH TO STOP LAYER -307 IN-SITU ASHING (REMOVE IMAGE LAYER(S)) -309 -311 STOP LAYER ETCH -313 IN-SITU PLASMA CLEANING Figure 3